

P-Ch 30V Fast Switching MOSFETs

- ★ Green Device Available
- ★ Super Low Gate Charge
- ★ Excellent CdV/dt effect decline
- ★ Advanced high cell density Trench technology

Product Summary

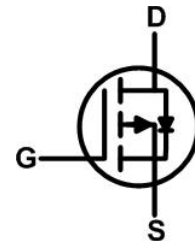
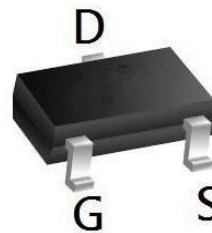


BVDSS	RDSON	ID
-30V	23mΩ	-7.0A

Description

The UD30P07L is the high cell density trenched P-ch MOSFETs, which provides excellent RDSON and efficiency for most of the small power switching and load switch applications. The UD30P07L meet the RoHS and Green Product requirement with full function reliability approved.

SOT23-3L Pin Configuration



Absolute Maximum Ratings (T_A=25°C unless otherwise specified)

Symbol	Parameter		Max.	Units
V _{DSS}	Drain-Source Voltage		-30	V
V _{GSS}	Gate-Source Voltage		±20	V
I _D	Continuous Drain Current	T _A = 25°C	-7	A
		T _A = 100°C	-4.6	A
I _{DM}	Pulsed Drain Current ^{note1}		-18	A
P _D	Power Dissipation	T _A = 25°C	1.5	W
R _{θJA}	Thermal Resistance, Junction to Ambient		61.7	°C/W
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +150	°C

Electrical Characteristics ($T_J=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D = -250μA	-30	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = -30V, V _{GS} =0V,	-	-	-1	μA
I _{GSS}	Gate to Body Leakage Current	V _{DS} =0V, V _{GS} = ±20V	-	-	±100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D = -250μA	-1.0	-1.5	-2.5	V
R _{DS(on)}	Static Drain-Source on-Resistance note3	V _{GS} = -10V, I _D = -7A	-	23	35	mΩ
		V _{GS} = -4.5V, I _D = -4A	-	27	54	
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} = -15V, V _{GS} =0V, f=1.0MHz	-	982	-	pF
C _{oss}	Output Capacitance		-	135	-	pF
C _{rss}	Reverse Transfer Capacitance		-	109	-	pF
Q _g	Total Gate Charge	V _{DS} = -15V, I _D = -4A, V _{GS} = -10V	-	10	-	nC
Q _{gs}	Gate-Source Charge		-	2	-	nC
Q _{gd}	Gate-Drain(“Miller”) Charge		-	2.7	-	nC
Switching Characteristics						
t _{d(on)}	Turn-on Delay Time	V _{DD} = -15V, I _D = -7A, V _{GS} = -10V, R _{GEN} =2.5Ω	-	11	-	ns
t _r	Turn-on Rise Time		-	19	-	ns
t _{d(off)}	Turn-off Delay Time		-	45	-	ns
t _f	Turn-off Fall Time		-	26	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain to Source Diode Forward Current		-	-	-7	A
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	-28	A
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} =0V, I _S = -7A	-	-0.8	-1.2	V

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$

Typical Performance Characteristics

Figure 1: Output Characteristics

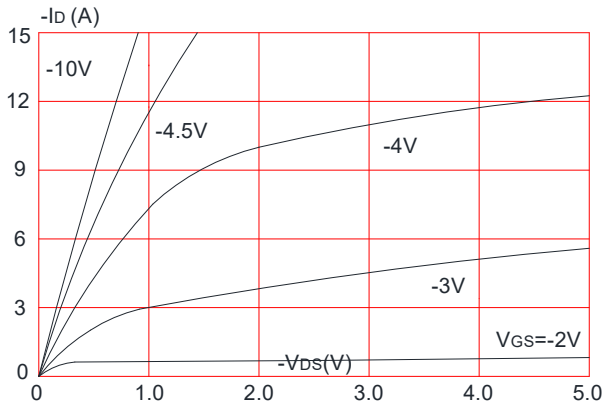


Figure 2: Typical Transfer Characteristics

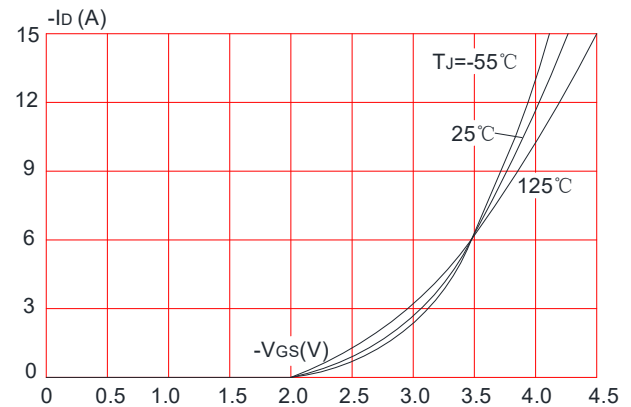


Figure 3: On-resistance vs. Drain Current

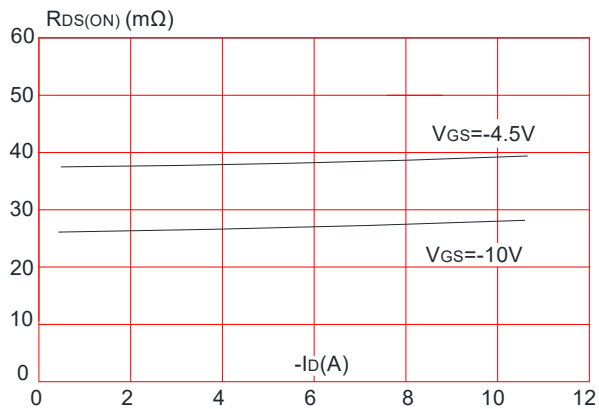


Figure 4: Body Diode Characteristics

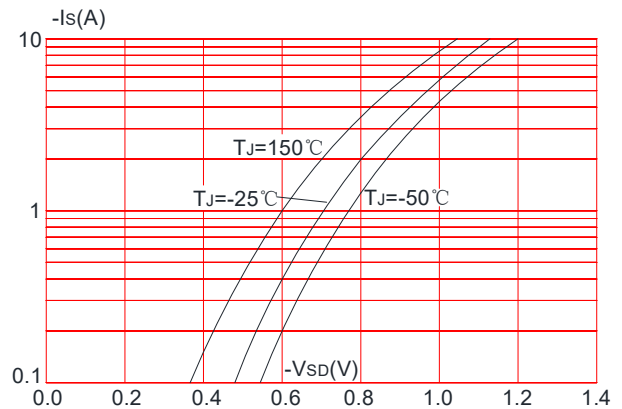


Figure 5: Gate Charge Characteristics

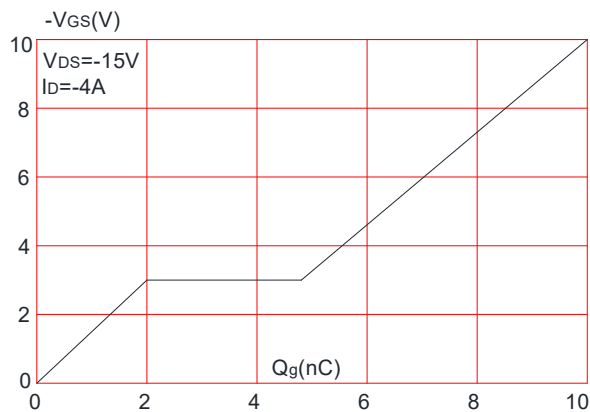
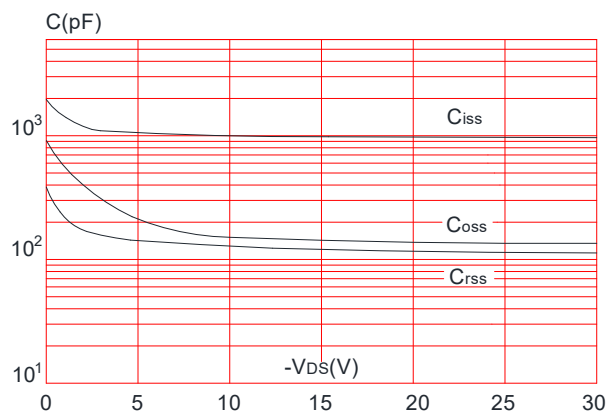


Figure 6: Capacitance Characteristics



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Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

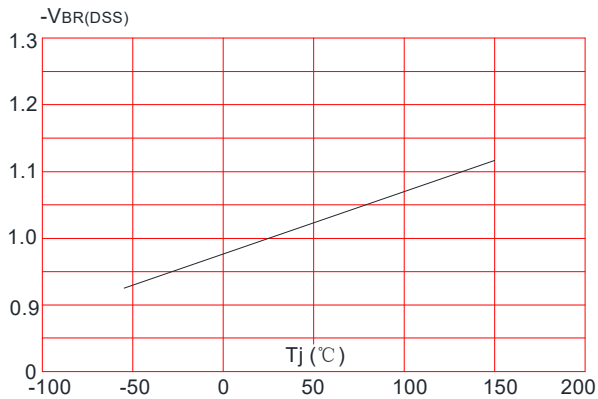


Figure 8: Normalized on Resistance vs. Junction Temperature

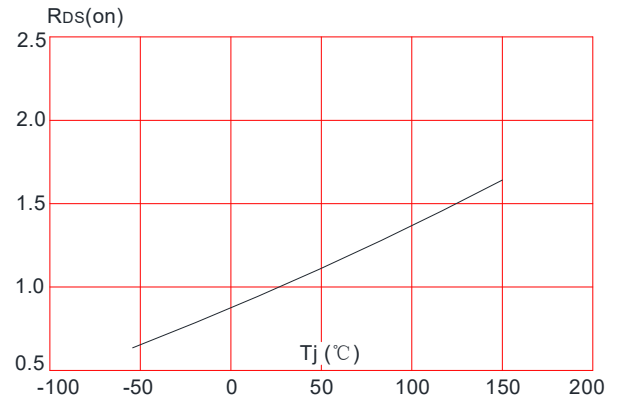


Figure 9: Maximum Safe Operating Area

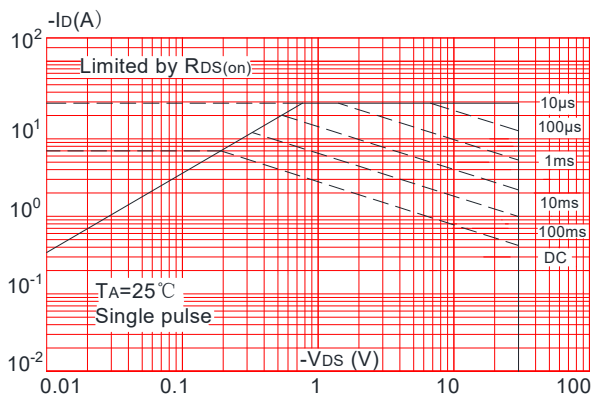
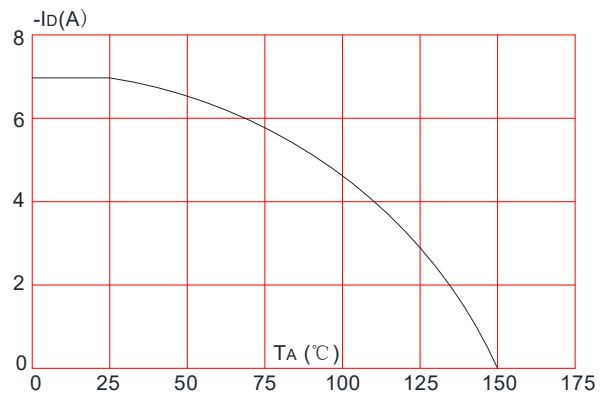
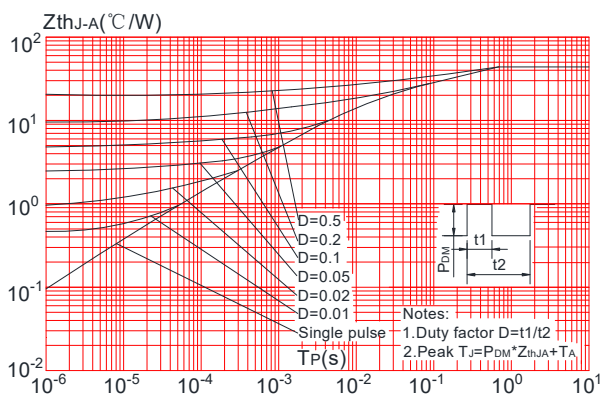


Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

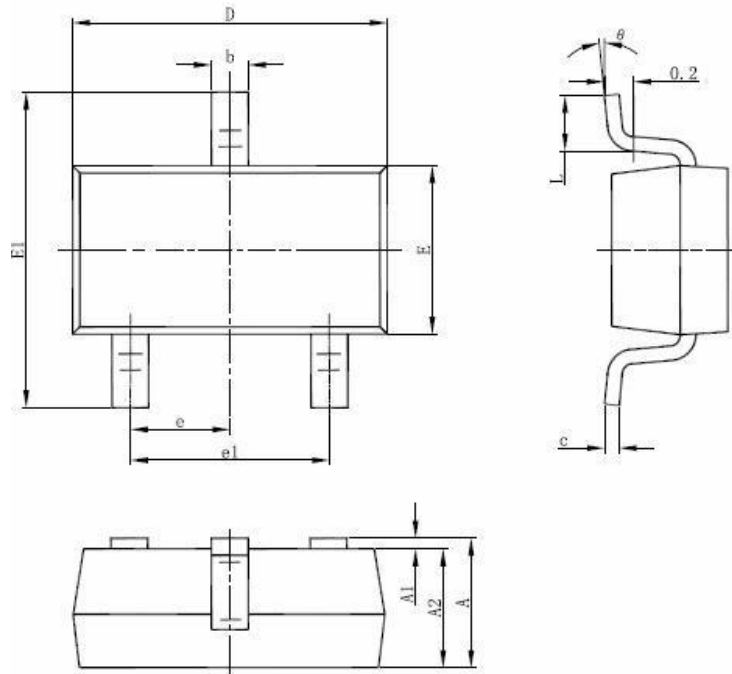


Maximum Effective Transient Thermal Impedance, Junction-to-Ambient





SOT-23-3L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E	1.500	1.700	0.059	0.067
E1	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°